



## **Preliminary Information**

# DPI2100P45A5200

## **Press-Pack FRD**

Replaces DS6218-1 DS6218-2 July 2018 (LN35909)

### **FEATURES**

- Wide safe operating area
- 10µs short circuit withstand
- Outstanding thermal cycling capability
- All-IGBT configuration
- High tolerance of non-uniform clamping pressure

### **APPLICATIONS**

- High voltage DC transmission
- Flexible AC transmission systems
- High reliability inverters
- Motor controllers

## **ORDERING INFORMATION**

Order As:

DPI2100P45A5200

Note: When ordering, please use the complete part number

## **KEY PARAMETERS**

$V_{CES}$		4500V
$V_{CE(sat)}$	(typ)	2.4V
l <sub>c</sub> ` ´	(max)	2100A
I <sub>C(PK)</sub>	(max)	4200A

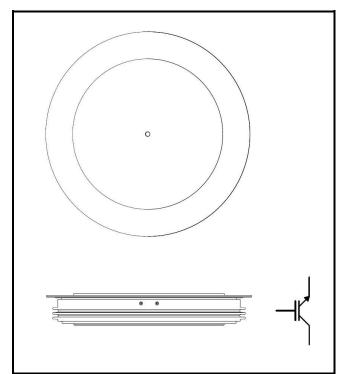


Fig.1 Circuit configuration



Fig. 2 Package



## **ABSOLUTE MAXIMUM RATINGS**

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T<sub>case</sub> = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
$V_{CES}$	Collector-emitter voltage	$V_{GE} = 0V$	4500	V
$V_{GES}$	Gate-emitter voltage	-	±20	V
I <sub>C</sub>	Continuous collector current	T <sub>case</sub> = 95°C	2100	А
I <sub>C(PK)</sub>	Peak collector current	1ms, T <sub>j</sub> = 125°C	4200	Α
P <sub>max</sub>	Max. transistor power dissipation	T <sub>case</sub> = 25°C, T <sub>j</sub> = 125°C	22.7	kW

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
R <sub>th(j-c)</sub> *	Thermal resistance – junction to case (collector side)	DC	-	0.0044	°C/W
R <sub>th(c-h)</sub> *	Thermal resistance – case to heatsink (collector side)	Clamping force 70kN (with mounting compound)	-	0.0018	°C/W
T <sub>vj</sub>	Virtual junction temperature	-	-	125	°C
T <sub>stg</sub>	Storage temperature range	-	-40	125	°C
F <sub>m</sub>	Clamping force	-	65	75	kN

#### Note:

<sup>\*</sup> Heat transfer occurs primarily through the collector side of the device.



## **ELECTRICAL CHARACTERISTICS**

 $T_{case}$  = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I <sub>CES</sub>	Collector cut-off current	$V_{GE} = 0V$ , $V_{CE} = V_{CES}$			5	mA
		$V_{GE} = 0V$ , $V_{CE} = V_{CES}$ , $T_{case} = 125$ °C		20	60	mA
I <sub>GES</sub>	Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			10	μΑ
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 260$ mA, $V_{GE} = V_{CE}$		6.1		V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	$V_{GE} = 15V$ , $I_C = 2100A$ , $T_j = 25$ °C		2.4		V
		$V_{GE} = 15V$ , $I_C = 2100A$ , $T_j = 125$ °C		2.8		V
Qg	Gate charge	V <sub>GE</sub> = ±15V		38		μC
SC <sub>Data</sub>	Short circuit current, I <sub>SC</sub>	$T_{j} = 125^{\circ}C$ , $V_{CC} = 3400V$ $t_{p} \le 10\mu s$ , $V_{GE} \le 15V$ $V_{CE (max)} = V_{CES} - L^{*} x dI/dt$ IEC 60747-9		10000		А

## Note:

<sup>\*</sup> L is the circuit inductance



## **ELECTRICAL CHARACTERISTICS**

T<sub>case</sub> = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
t <sub>d(off)</sub>	Turn-off delay time	I <sub>C</sub> = 2100A		4700		ns
t <sub>f</sub>	Fall time	$V_{GE} = \pm 15V$		1900		ns
E <sub>OFF</sub>	Turn-off energy loss	$V_{\text{CE}} = 2800V$ $R_{\text{G(ON)}} = 1.5\Omega$ $R_{\text{G(OFF)}} = 4.7\Omega$ $C_{\text{GE}} = 330\text{nF}$		9900		mJ
t <sub>d(on)</sub>	Turn-on delay time			760		ns
t <sub>r</sub>	Rise time	L <sub>S</sub> ~ 220nH Freewheel diode type		420		ns
E <sub>ON</sub>	Turn-on energy loss	Dynex DPF2100P45A0052		6400		mJ

T<sub>case</sub> = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
t <sub>d(off)</sub>	Turn-off delay time	$I_{C}=2100A$ $V_{GE}=\pm15V$ $V_{CE}=2800V$ $R_{G(ON)}=1.5\Omega$ $R_{G(OFF)}=4.7\Omega$ $C_{GE}=330nF$ $L_{S}\sim220nH$ Freewheel diode type $Dynex\ DPF2100P45A0052$		4800		ns
t <sub>f</sub>	Fall time			2900		ns
E <sub>OFF</sub>	Turn-off energy loss			11000		mJ
t <sub>d(on)</sub>	Turn-on delay time			720		ns
t <sub>r</sub>	Rise time			440		ns
E <sub>ON</sub>	Turn-on energy loss			8800		mJ



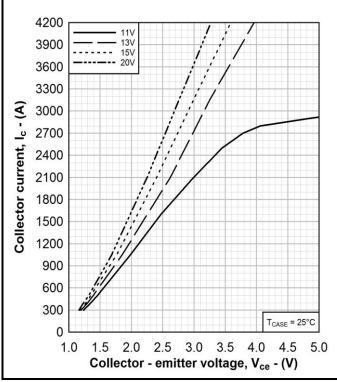


Fig. 3 Typical output characteristics

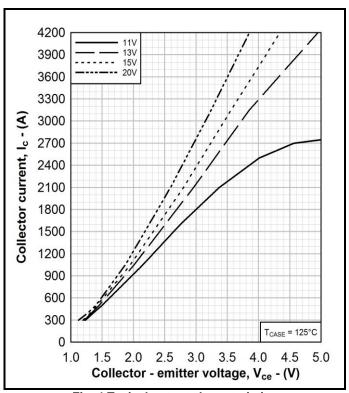


Fig. 4 Typical output characteristics

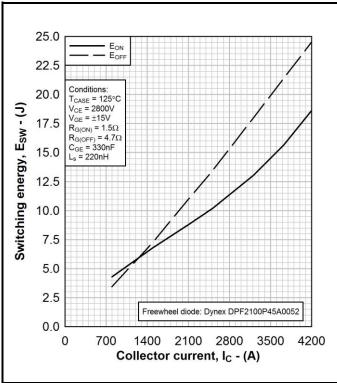


Fig. 5 Typical switching energy vs. collector current

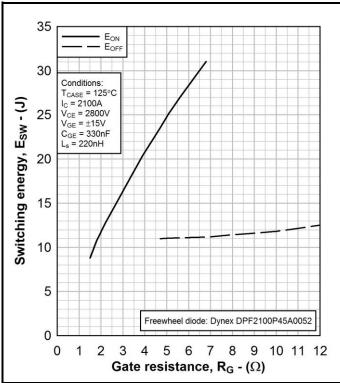


Fig. 6 Typical switching energy vs. gate resistance



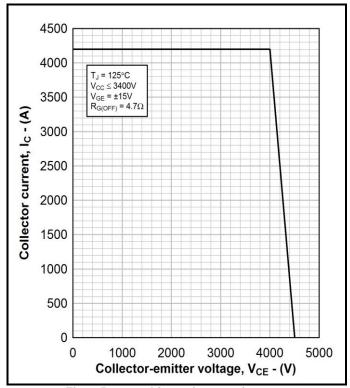


Fig. 7 Reverse bias safe operating area

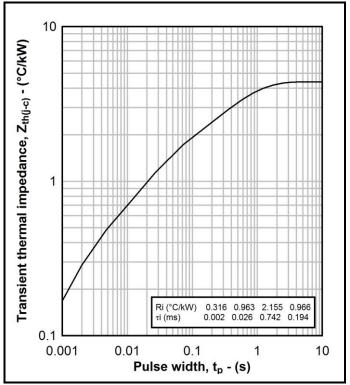


Fig. 8 Thermal impedance



## **PACKAGE DETAILS**

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.

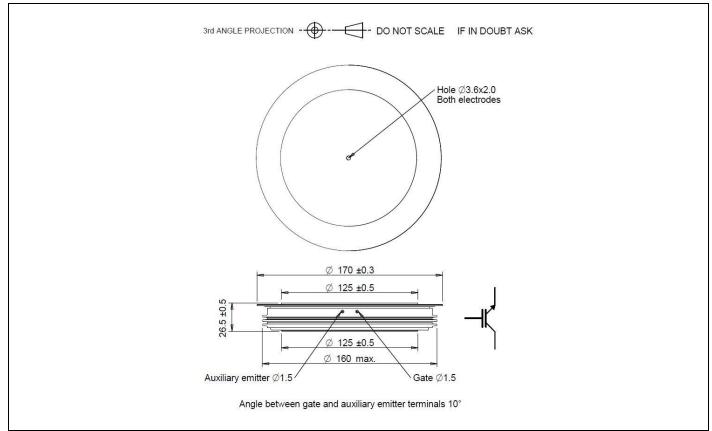


Fig. 9 Package outline



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The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

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**Target Information:** This is the most tentative form of information and represents a very preliminary specification.

No actual design work on the product has been started.

**Preliminary Information:** The product design is complete and final characterisation for volume production is in progress.

The datasheet represents the product as it is now understood but details may change.

No Annotation: The product has been approved for production and unless otherwise notified by Dynex any

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